

NPN High-Voltage Transistor

FJV42

SOT-23 (TO-236) **CASE 318**

ABSOLUTE MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	350	V
V _{CBO}	Collector-Base Voltage	350	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	500	mA
T _{STG}	Storage Temperature Range	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Note 1)

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter	Value	Unit
P _D	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

^{1.} PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

MARKING DIAGRAM



1DF = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
FJV42MTF	SOT-23 (Pb-Free)	3,000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

FJV42

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter	Conditions	Min	Max	Unit
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage (Note 2)	I _C = 5.0 mA, I _B = 0	350		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	350		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA, I _C = 0	6		V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 200 V, I _E = 0		0.1	μΑ
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 5.0 V, I _C = 0		0.1	μΑ
h _{FE}	DC Current Gain (Note 2)	I _C = 1.0 mA, V _{CE} = 10 V	25		
		I _C = 10 mA, V _{CE} = 10 V	40		
		I _C = 30 mA, V _{CE} = 10 V	40		
V _{CE} (sat)	Collector-Emitter Saturation Voltage (Note 2)	I _C = 20 mA, I _B = 2.0 mA		0.5	V
V _{BE} (sat)	Base-Emitter Saturation Voltage (Note 2)	I _C = 20 mA, I _B = 2.0 mA		0.9	V
f _T	Current Gain – Bandwidth Product	I _C = 10 mA, V _{CE} = 20 V, f = 100 MHz	50		MHz
C _{cb}	Output Capacitance	V _{CB} = 20 V, I _E = 0, f = 1.0 MHz		3	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Pulse test: Pulse width $\leq 300~\mu s,$ duty cycle $\leq 2\%$

TYPICAL PERFORMANCE CHARACTERISTICS

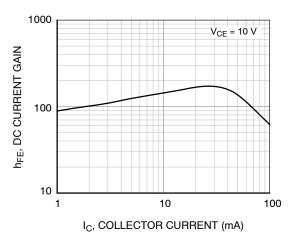


Figure 1. DC Current Gain

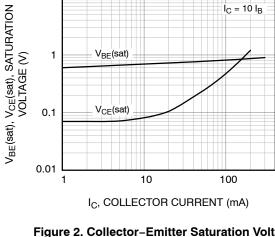


Figure 2. Collector–Emitter Saturation Voltage and Base–Emitter Saturation Voltage

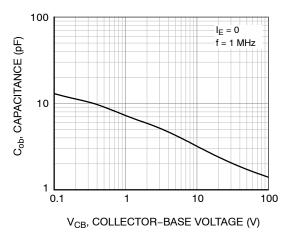


Figure 3. Collector-Base Capacitance

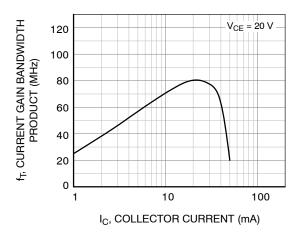


Figure 4. Current Gain Bandwidth Product

MILLIMETERS

MIN

0.89

0.01

0.37

0.08

2.80

1.20

1.78

0.30

0.35

2.10

O°

NOM

1.00

0.06

0.44

0.14

2.90

1.30

1.90

0.43

0.54

2.40





SOT-23 (TO-236) 2.90x1.30x1.00 1.90P **CASE 318 ISSUE AU**

DATE 14 AUG 2024

MAX

1.11

0.10

0.50

0.20

3.04

1.40

2.04

0.55

0.69

2.64

10°

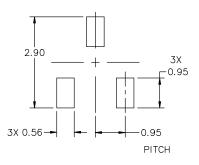




DETAIL "A" Scale 3:1







NOTES:

DIM

Α

Α1

b

С

D

Ε

е L

L1

HE

Τ

- DIMENSIONING AND TOLERANCING 1. PER ASME Y14.5M, 2018. CONTROLLING DIMENSIONS:
- MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE
- BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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^{*}This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P CASE 318 ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR			
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	2. CATHODE 2.	2: STYLE 13: CATHODE PIN 1. SOURCE CATHODE 2. DRAIN ANODE 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	2. ANODE 2.	3: STYLE 19: NO CONNECTION PIN 1. CATHODE CATHODE 2. ANODE ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT			STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE			

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